**X.J.Fan<sup>1</sup>** P R a USA,345 S a b ∟ R a , B a Man ,NY 10510 - a **∢** ∟ ∟1.an@...

J. Zhou

Da, ו M an a E בי חי, La a Un , Bau ו, TX 77710 - a: וו. נ@aa. נ

**G. Q. Zhang** P -CFT, P.O. B≼ 218, 5600 MD E n n, T N an - a : \_\_\_\_ an @ .

**L. J. Ernst** D. Un T. M. 2,2628 CDD ., T. N. an - a : . . . n.@ b........

## A Micromechanics-Based Vapor Pressure Model in Electronic Packages

A complete vapor pressure model based on a micromechanics approach is developed in this paper. The model can be extended to calculate the initial vapor pressure as traction loading subjected to the interfaces after the delamination. The impact of the vapor pressure induced expanison on the material's deformation is discussed. [DOI: 10.1115/1.1939027]

## 1 Introduction

Polymer materials have wide applications in microelectronic packaging. Some polymer materials are used in bulk form, such as encapsulant (molding compound) and carrier or printed circuit boards (FR4 and BT). Some polymer materials are used as adhesives, such as die-attach, underfill, or other structural and thermal adhesives. Polymers are also used in thin or thick film as an isolation layer, such as a solder mask on a printed circuit board or passivation layer in the wafer level.

Despite the diversities of the chemistry and compositions, the polymer materials applied in microelectronics can be either thermoset or thermoplastic materials [1]. Both types of materials have a glass transition temperature around which the material properties, such as the CTE and Young's modulus, are very sensitive to temperature.

Another common feature of polymer materials is the high po-

$$\alpha_{\rm D1} \frac{\partial C_1}{\partial n} = \alpha_{\rm D2} \frac{\partial C_2}{\partial n} \tag{3}$$

where 1 and 2 represent different materials, respectively, and *S* is the solubility. The solubility *S* is related to the saturated concentration  $C_{\text{sat}}$  by

$$S = C_{\rm sat} / p_{\rm ext} \tag{4}$$

where  $p_{\text{ext}}$  is the ambient vapor pressure under the given humid conditions.

In order to numerically solve Eq. (1) in a multiple-material system (e.g., by finite element method), the following variable with continuity at the interface can be defined [2]

$$\varphi = C/S \tag{5}$$

or equivalently, according to Eq. (4)

$$w = C/C_{\rm sat} \tag{6}$$

In order to illustrate the nature of the moisture diffusion in plastic materials, we consider an example of a simple transient moisture diffusion problem in a slab, with the boundary conditions as shown in Fig. 1. The thickness of 2 mm is taken as a typical value. The material properties (e.g., a typical mold compound), together with the ambient humid conditions for three types of moisture preconditioning are listed in Table 1 [2]. The solution can be represented as [3]

$$C(x,t) = C_{\text{sat}} \left[ 1 - \sum_{n=0}^{\infty} \left[ w \right] \right]$$

$$f = \frac{dV_f}{dV} \quad 0 < f \le 1 \tag{11}$$

The following relation between  $\rho$  and C can be obtained

$$\rho = \frac{\mathrm{d}m}{\mathrm{d}V_f} = \frac{\mathrm{d}m}{\mathrm{d}V}\frac{\mathrm{d}V}{\mathrm{d}V_f} = C/f \tag{12}$$

As discussed before, the saturated moisture concentration  $C_{\text{sat}} = 41\rho_{\text{ext}}$  at 85°C/85RH condition for a typical mold compound. Assume that the void volume fraction *f* is 0.05, Eq. (12) gives  $\rho = 820\rho_{\text{ext}}$ . This number clearly shows that how much moisture a

$$C_0/f_0 > \rho_g(T_0)$$
 and  $\frac{C_0}{f} [1 - 3\alpha(T - T_0)] < \rho_g(T)$  (30)

The phase transition temperature  $T_1$ , where the moisture is just fully vaporized, should be determined first according to Eq. (14), which can be rewritten as

$$\frac{C_0}{f(T_1)} [1 - 3\alpha(T_1 - T_0)] = \rho_g(T_1)$$
(31)

Then from  $T_1$  to temperature T the Eq. (18) can be used with the reference state  $(p_r, f_r, T_r, C_r)$  to be substituted by  $(p(T_1), f(T_1), T_1, C(T_1))$ , as follows:

$$p(T) = p(T_1) \frac{T}{T_1} \frac{f(T_1)C}{fC(T_1)} = p_g(T_1) \frac{T}{T_1} \frac{f(T_1)C}{fC(T_1)}$$
$$= p_g(T_1) \frac{T}{T_1} \frac{f(T_1)}{f} \frac{1 - 3\alpha(T - T_0)}{1 - 3\alpha(T_1 - T_0)}$$
(32)

Now the equations for calculating the vapor pressure are complete, which can be summarized as follows:

Case 1: when  $C_0/f_0 \leq \rho_g(T_0)$ 

$$p(T) = \frac{C_0 p_g(T_0)}{\rho_g(T_0) f} \frac{T}{T_0} [1 - 3\alpha(T - T_0)]$$
(33)

Case 2: when  $(C_0/f)[1-3\alpha(T-T_0)] \ge \rho_g(T)$ 

$$p(T) = p_g(T) \tag{34}$$

Case 3: when  $C_0/f_0 > \rho_g(T_0)$ , and  $(C_0/f)[1-3\alpha(T-T_0)] < \rho_g(T)$ 

$$p(T) = p_g(T_1) \frac{T}{T_1} \frac{f(T_1)}{f} \frac{1 - 3\alpha(T - T_0)}{f}$$

rated vapor pressure, i.e.,  $p = p_g(T=220 \text{ °C}) = 2.32$  MPa. The vapor pressure with such a magnitude has significant effect on the void behavior, which was discussed in Ref. [7]. Questions remain that how to measure the initial void volume

Questions remain that how to measure the initial void volume fraction  $f_0$ . An approximate method in estimating the initial void volume fraction was proposed [6] by using the moisture absorption test. FroT8tion

the delaminated surfaces. After the moisture-diffusion modeling is performed, the averaged moisture concentration can be calculated according to Eq. (44). When

$$C^{\text{ave}} \ge \rho_g(T) \tag{45}$$